

isc Silicon NPN Power Transistor

2SC6082

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DESCRIPTION

- Large current capacitance
- High speed switching
- · Low saturation voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

SYMBOL

Vсво

VCEO

VEBO

lc

lΒ

ICP

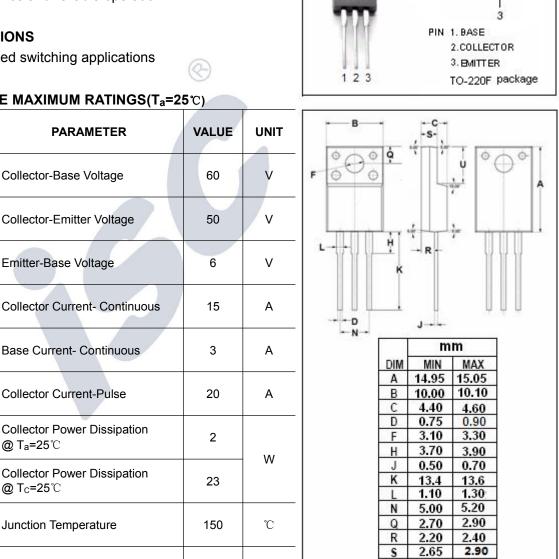
 P_{C}

ТJ

Tstg

• High speed switching applications





°C

-55~150

1

Storage Temperature Range

@ Ta=25℃

@ Tc=25°C

U

6.40

6.60



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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25\,^\circ\!\!\!\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 7.5A; I _B = 0.375A			0.4	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 7.5A; I _B = 0.375A			1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40V; I _E = 0			10	μ Α
h _{FE-1}	DC Current Gain	I _C = 330mA; V _{CE} = 2V	200		560	
h _{FE-2}	DC Current Gain	I _C = 10A; V _{CE} = 2V	50			
tstg	Storage Time			560		ns
t _f	Fall Time	I _C = 5A, I _{B1} = 0.25A; I _{B2} = -0.25A		37		ns

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